

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	8	118/719.ccls. and (chamber with pressure with higher with prevent)	US-PGPUB; USPAT	OR	ON	2004/06/10 11:26
S2	1	("20010040145").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/02/26 10:13
S3	196	156/345.24	US-PGPUB; USPAT	OR	ON	2003/08/22 16:30
S4	600	((156/345.24) or (156/345.51) or (156/345.52) or (156/345.53)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/08/22 16:31
S5	177	((((156/345.24) or (156/345.51) or (156/345.52) or (156/345.53)).CCLS.) and (control\$3 with (substrate wafer target) with temperature)	US-PGPUB; USPAT	OR	ON	2004/06/09 19:43
S6	4	(((((156/345.24) or (156/345.51) or (156/345.52) or (156/345.53)).CCLS.) and (control\$3 with (substrate wafer target) with temperature)) and ((high with densit\$3) same (low with ion\$6))	US-PGPUB; USPAT	OR	ON	2003/08/22 17:14
S7	728	(156/345.\$CCLS.) and (control\$3 with (substrate wafer target) with temperature)	US-PGPUB; USPAT	OR	ON	2004/06/09 19:44
S8	142	(156/345.\$CCLS.) and (control\$3 with (substrate wafer target) with temperature with etch\$3)	US-PGPUB; USPAT	OR	ON	2004/06/09 19:44
S9	166	(156/345.\$CCLS.) and (control\$4 with (substrate wafer target) with temperature with etch\$3)	US-PGPUB; USPAT	OR	ON	2004/06/09 19:46
S10	131	(156/345.\$CCLS.) and (control\$4 with (substrate wafer target) with temperature with during with (process\$3 treatm\$3))	US-PGPUB; USPAT	OR	ON	2004/06/09 19:46
S11	2	(156/345.\$CCLS.) and (control\$4 with (substrate wafer target) with temperature with during with (process\$3 treatm\$3) with damag\$3)	US-PGPUB; USPAT	OR	ON	2004/06/09 19:47
S12	39	(control\$4 with (substrate wafer target) with temperature with during with (process\$3 treatm\$3) with damag\$3)	US-PGPUB; USPAT	OR	ON	2004/06/09 19:56
S13	0	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 204/298.25.ccls. 204/298.35.ccls.) and (156/345.24.ccls. 156/345.27.ccls. 204/298.03.ccls. 204/298.32.ccls.) and (control\$4 with (substrate wafer workpiece) with temperature with during with (process\$3 treatm\$3) with damag\$3)	US-PGPUB; USPAT	OR	ON	2004/06/09 20:00
S14	0	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 204/298.25.ccls. 204/298.35.ccls.) and (156/345.24.ccls. 156/345.27.ccls. 204/298.03.ccls. 204/298.32.ccls.) and (control\$4 with (substrate wafer workpiece) with temperature with damag\$3)	US-PGPUB; USPAT	OR	ON	2004/06/09 20:00
S15	79	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 204/298.25.ccls. 204/298.35.ccls.) and (156/345.24.ccls. 156/345.27.ccls. 204/298.03.ccls. 204/298.32.ccls.)	US-PGPUB; USPAT	OR	ON	2004/06/09 20:00
S16	24	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 204/298.25.ccls. 204/298.35.ccls.) and (156/345.24.ccls. 156/345.27.ccls. 204/298.03.ccls. 204/298.32.ccls.) and (control\$4 with temperature)	US-PGPUB; USPAT	OR	ON	2004/06/09 20:11
S17	0	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 204/298.25.ccls. 204/298.35.ccls.) and (156/345.24.ccls. 156/345.27.ccls. 204/298.03.ccls. 204/298.32.ccls.) and (control\$4 with temperature with magnet\$ with propert\$3)	US-PGPUB; USPAT	OR	ON	2004/06/09 20:12
S18	1	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 204/298.25.ccls. 204/298.35.ccls.) and (control\$4 with temperature with magnet\$ with propert\$3)	US-PGPUB; USPAT	OR	ON	2004/06/09 20:12
S19	3	(156/345.24.ccls. 156/345.27.ccls. 204/298.03.ccls. 204/298.32.ccls.) and (control\$4 with temperature with magnet\$ with propert\$3)	US-PGPUB; USPAT	OR	ON	2004/06/09 20:13
S20	133	(control\$4 with temperature with magnet\$ with propert\$3)	EPO; JPO; DERWENT	OR	ON	2004/06/09 20:13
S21	2	(control\$4 with temperature with magnet\$ with propert\$3 with (during) with (treat\$4 process\$4))	EPO; JPO; DERWENT	OR	ON	2004/06/09 20:14

S22	11	(control\$4 with temperature with magnet\$ with propert\$3 with (during) with (treat\$4 process\$4))	US-PGPUB; USPAT	OR	ON	2004/06/09 20:20
S23	65	(control\$4 with temperature with magnet\$ with propert\$3 with (treat\$4 process\$4))	US-PGPUB; USPAT	OR	ON	2004/06/09 20:20
S24	65	(control\$4 with temperature with magnet\$ with propert\$3 with (treat\$4 process\$4))	US-PGPUB; USPAT	OR	ON	2004/06/09 20:21
S25	24	(control\$4 with temperature with magnet\$ with propert\$3 with (treat\$4 process\$4))	EPO; JPO; DERWENT	OR	ON	2004/06/09 20:21
S26	788	(156/345.\$.\$ccls. 118/715/733.\$.\$ccls.) and ((control\$4 with temperature) with (substrate wafer workpiece))	US-PGPUB; USPAT	OR	ON	2004/06/10 11:27
S27	177	(156/345.\$.\$ccls. 118/715/733.\$.\$ccls.) and ((control\$4 with temperature) with (substrate wafer workpiece) with (during))	US-PGPUB; USPAT	OR	ON	2004/06/10 11:27
S28	13	(156/345.\$.\$ccls. 118/715/733.\$.\$ccls.) and ((control\$4 adj temperature) adj (substrate wafer workpiece) adj (during))	US-PGPUB; USPAT	OR	ON	2004/06/10 13:13
S29	22	(156/345.\$.\$ccls.) and ((low adj temperature) adj (etch\$3))	US-PGPUB; USPAT	OR	ON	2004/06/10 13:14
S30	10	("5571366" "5572366" "5645683" "5695564" "5695654" "5700734" "5756401" "6008139" "6046116" "6087264"). PN.	USPAT	OR	ON	2004/06/10 13:17
S31	18	(156/345.\$.\$ccls. "216"/\$.\$ccls.) and (plasma same (low adj ion adj energy) same (high adj density))	US-PGPUB; USPAT	OR	ON	2004/06/10 15:53
S32	1	"10/080,539"	US-PGPUB; USPAT	OR	ON	2004/06/10 15:59
S33	100	kagoshima-akira.in. yamamoto-hideyuki.in. torii-yoshimi.in.	US-PGPUB; USPAT	OR	ON	2004/06/10 16:00
S34	31	(kagoshima-akira.in. yamamoto-hideyuki.in. torii-yoshimi.in.) and (control\$4 with etch\$3) and ash\$3	US-PGPUB; USPAT	OR	ON	2004/06/10 16:05
S35	0	(204/298.35.ccls. 204/298.25.ccls. 204/298.32.ccls.) and (etch\$3 same ash\$3 same control\$4 same (transfer\$4 transport\$4) same order)	US-PGPUB; USPAT	OR	ON	2004/06/10 16:07
S36	46	(204/298.35.ccls. 204/298.25.ccls. 204/298.32.ccls.) and (control\$4 same (transfer\$4 transport\$4) same order)	US-PGPUB; USPAT	OR	ON	2004/06/10 16:07
S37	3	(204/298.35.ccls. 204/298.25.ccls. 204/298.32.ccls.) and ((order near control\$4) same (transfer\$4 transport\$4))	US-PGPUB; USPAT	OR	ON	2004/06/10 16:08
S38	2	((("5769952") or ("6048435"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/04/06 16:46